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A Product Line of
Diodes Incorporated

PI3WVR626

2:1 MIPI 2-Data Lane Switch

Description

The DIODES PI3WVR626 is a two-data-lane MIPI switch. This 6 channel single-pole, double-throw (SPDT) switch is optimized for switching between two high-speed (HS) or low-power (LP) MIPI signal. The PI3WVR626 is designed for the MIPI specification and allows connection to CSI/DSI, C-PHY/D-PHY module.

Application(s)

- Cellular Phones, Smart Phones
- Tablets
- Laptops
- Displays

Features

- 3-lane, 2:1 Switches that support D-PHY and C-PHY
- Data Rate Support: up to 3.5Gsps C-PHY, up to 4.5Gb/s D-PHY.
- Bandwidth: 6GHz Typical
- Low Crosstalk: -35 dB@1.25 GHz
- Input Signals 0 to 1.3V
- R_{ON}: 5.0Ω Typical LP & HS MIPI
- ΔR_{ON}: 0.2Ω Typical LP & HS MIPI
- R_{ON_FLAT}: 0.1Ω Typical LP & HS MIPI
- I_{CC}: 11μA Typical
- Skew of Opposite Transitions of the Same Output: 5ps Typical
- V_{DD} Operating Range: 1.5V to 3.6V
- ESD Tolerance: 2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. “Green” Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
  https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green):
  - 24-Pin, X1QFN (2.5mm x 2.5mm) (XEB)

Notes:

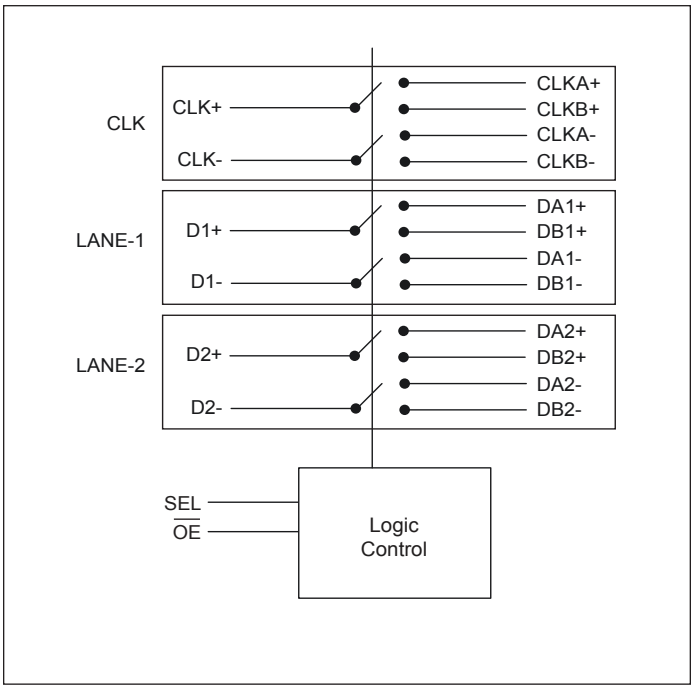
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

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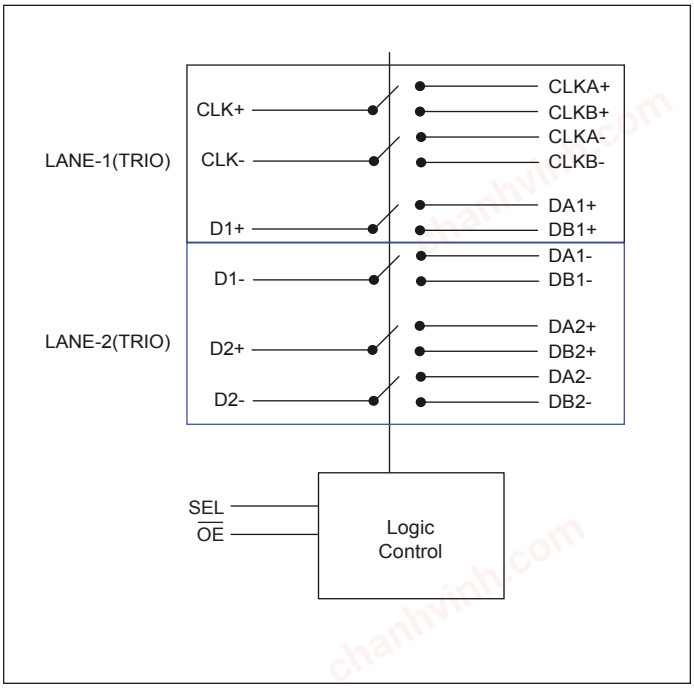
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Block Diagram

PI3WVR626 D-PHY Application



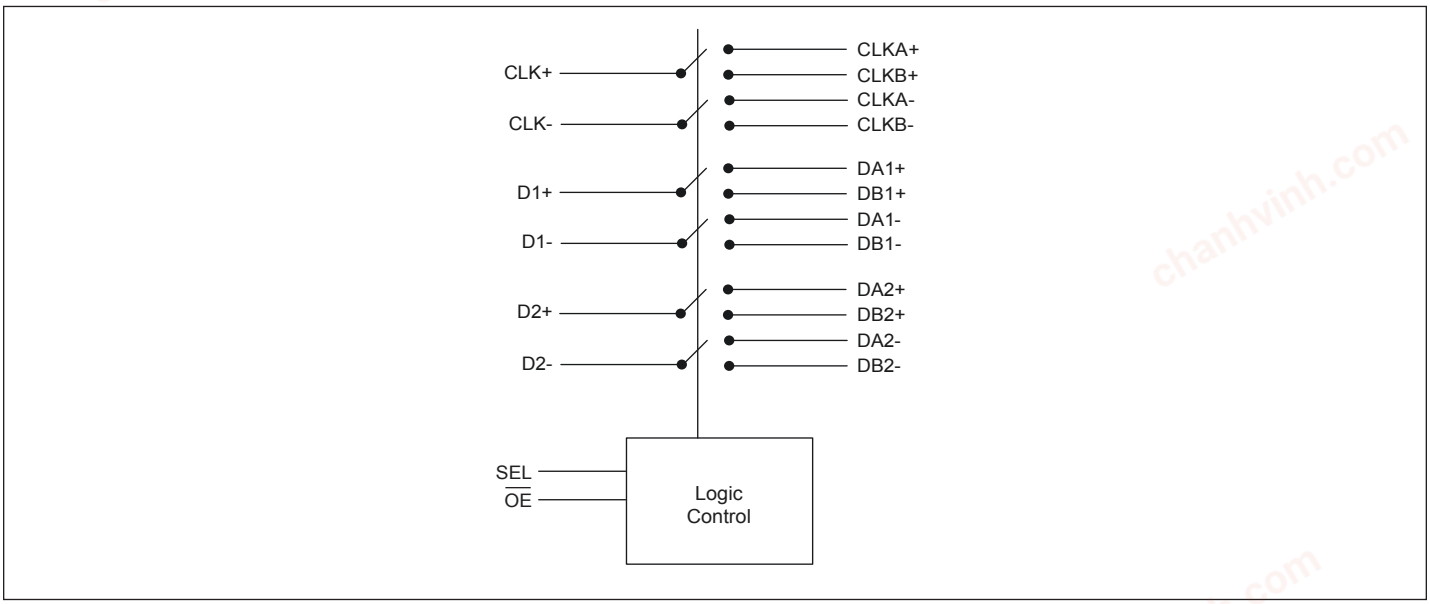
PI3WVR626 C-PHY Application



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Block Diagram



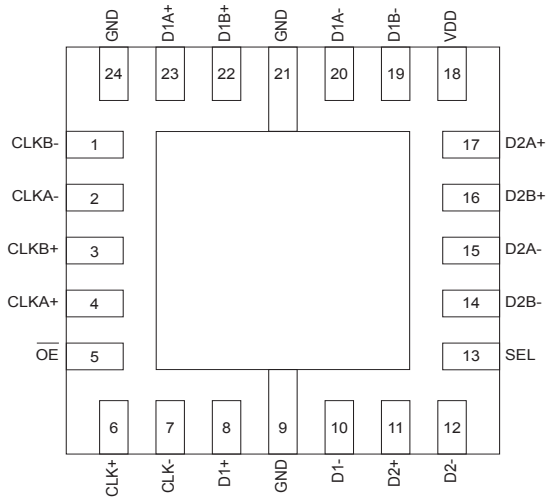
Truth Table

SEL	$\overline{OE}$	Function
LOW	LOW	CLK+ = CLKA+, CLK- = CLKA-, Dn(+/-) = DAn(+/-)
HIGH	LOW	CLK+ = CLKB+, CLK- = CLKB-, Dn(+/-) = DBn(+/-)
X	HIGH	Clock and Data Ports High Impedance

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Pin Configuration



Pin Description

Pin#	Pin Name	Type	Description
18	V_{DD}	Power	1.5V to 3.3V power supply
9, 21, 24	GND	Ground	Ground
5	$\overline{OE}$	I	Output enable. if OE is low, IC is enabled. if OE is high, IC is power down and all I/Os are Hi-Z
13	SEL	I	Switch logic control
14	D2B-	I/O	Negative differential signal 2 for port B
16	D2B+	I/O	Positive differential signal 2 for port B
15	D2A-	I/O	Negative differential signal 2 for port A
17	D2A+	I/O	Positive differential signal 2 for port A
12	D2-	I/O	Negative differential signal 2 for COM port
11	D2+	I/O	Positive differential signal 2 for COM port
19	D1B-	I/O	Negative differential signal 1 for port B
22	D1B+	I/O	Positive differential signal 1 for port B
20	D1A-	I/O	Negative differential signal 1 for port A
23	D1A+	I/O	Positive differential signal 1 for port A
10	D1-	I/O	Negative differential signal 1 for COM port
8	D1+	I/O	Positive differential signal 1 for COM port
1	CLKB-	I/O	Clock negative differential signal for port B
3	CLKB+	I/O	Clock positive differential signal for port B
2	CLKA-	I/O	Clock negative differential signal for port A
4	CLKA+	I/O	Clock positive differential signal for port A
7	CLK-	I/O	Clock negative differential signal for COM port
6	CLK+	I/O	Clock positive differential signal for COM port

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Absolute Maximum Ratings

Above which useful life may be impaired. For user guidelines, not tested.

V_{CC}, Supply Voltage, ... -0.5V to 4.5V
V_{CNTRL}, DC Input Voltage ($\overline{OE}$, SEL)(1) ..... -0.5V to V_{CC}
V_{SW}, DC Switch I/O Voltage(1,2) ..... -0.3V to 2.5V
I_{IK}, DC Input Diodes Current ..... -50mA
I_{OUT}, DC Output Current 25mA
T_{STG}, Storage Temperature ..... -65°C to +150°C
Tj, Junction Temperature ..... 125°C
ESD:
Human Body Model, JEDEC: JESD22-A114, All Pins 2.0kV
Charged Device Model, JEDEC: JESD22-C101 ..... 1.0kV

Note:
Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Note:
1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.
2. V_{SW} refers to analog data switch paths.

Recommended Operating Conditions

The Recommended operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications.

Symbol	Description	Test Conditions	Min.	Max.	Units
V_{CC}	Supply Voltage		1.5	3.6	V
V_{CNTRL}	Control Input Voltage (SEL, $\overline{OE}$)(1)		0	V_{CC}	V
V_{SW}	Switch I/O Voltage (CLK-, D-, CLKA-, CLKB-, DA-, DB-)	HS Mode	0	0.5	V
		LP Mode	0	1.3	V
T_A	Operating Temperature		-40	+85	°C

Note:
1. The control inputs must be held HIGH or LOW; they must not float.

DC and Transient Characteristics

All typical values are at T_A = 25°C unless otherwise specified.

Symbol	Description	Test Conditions	V_{CC} (V)	T_A = -40°C to +85°C			Units
				Min.	Typ.	Max.	
V_{IK}	Clamp Diode Voltage ($\overline{OE}$, SEL)	I_{IN} = -18mA	1.5	-1.2		-0.6	V
V_{IH}	Input Voltage High	SEL, $\overline{OE}$	1.5 to 3.3	1.0			V
V_{IL}	Input Voltage Low	SEL, $\overline{OE}$	1.5 to 3.3			0.5	V
I_{IN}	Control Input Leakage ($\overline{OE}$, SEL)	V_{CNTRL} = 0 to V_{CC}	3.3	-1.0		1.0	µA
$I_{NO(OFF)}$ $I_{NC(OFF)}$	Off Leakage Current of Port CLKA-, DA-, CLKB- and DB-	V_{SW} = 0.0 ≤ DATA ≤ 1.3V	3.3	-1.0		1.0	µA
$I_{A(ON)}$	On Leakage Current of Common Ports (CLK-, D-)	V_{SW} = 0.0 ≤ DATA ≤ 1.3V	3.3	-1.0		1.0	µA
I_{OFF}	Power-Off Leakage Current (All I/O Ports)	V_{SW} = 0.0 or 1.3V	0	-5		5.0	µA

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Symbol	Description	Test Conditions	V_{CC} (V)	T_A = -40°C to +85°C			Units
				Min.	Typ.	Max.	
I_{OZ}	Off-State Leakage	V_{SW} = 0.0 ≤ DATA ≤ 1.3V, $\overline{OE}$ = High	3.6	-5		5.0	µA
$R_{ON_MIPI_HS}$	Switch On Resistance for HS MIPI	I_{ON} = -8mA, $\overline{OE}$ = 0V, SEL = V_{CC} or 0V, CLKA, CLKB, DB- or DA- = 0.2V	1.5		5		Ω
			2.5				
			3.3				
$R_{ON_MIPI_LP}$	Switch On Resistance for LP MIPI	I_{ON} = -8mA, $\overline{OE}$ = 0V, SEL = V_{CC} or 0V, CLKA, CLKB, DB- or DA- = 1.2V	1.5		5		Ω
			2.5				
			3.3				
$\Delta R_{ON_MIPI_HS}$	On Resistance Matching Between HS MIPI Channels(1)	I_{ON} = -8mA, $\overline{OE}$ = 0V, SEL = V_{CC} or 0V, CLKA, CLKB, DB- or DA- = 0.2V	1.5		0.2		Ω
			2.5				
			3.3				
$\Delta R_{ON_MIPI_LP}$	On Resistance Matching Between LP MIPI Channels(1)	I_{ON} = -8mA, $\overline{OE}$ = 0V, SEL = V_{CC} or 0V, CLKA, CLKB, DB- or DA- = 1.2V	1.5		0.2		Ω
			2.5				
			3.3				
$R_{ON_FLAT_MIPI_HS}$	On Resistance Flatness for HS MIPI	I_{ON} = -8mA, $\overline{OE}$ = 0V, SEL = V_{CC} or 0V, CLKA, CLKB, DB- or DA- = 0 to 0.5V	1.5		0.1		Ω
			2.5				
			3.3				
$R_{ON_FLAT_MIPI_LP}$	On Resistance Flatness for LP MIPI	I_{ON} = -8mA, $\overline{OE}$ = 0V, SEL = V_{CC} or 0V, CLKA, CLKB, DB- or DA- = 0 to 1.3V	1.5		0.1		Ω
			2.5				
			3.3				
I_{CC}	Quiescent Supply Current	V_{SEL} = 0 or V_{CC}, I_{OUT} = 0, $\overline{OE}$ = 0V	3.6		11	20	µA
I_{CCZ}	Quiescent Supply Current (High Impedance)	V_{SEL} = 0 or V_{CC}, I_{OUT} = 0, $\overline{OE}$ = 0V	3.6			1	µA
I_{CCT}	Increase in I_{CC} Current Per Control Voltage and V_{CC}	V_{SEL} = 0 or V_{CC}, $\overline{OE}$ = 1.5V	3.6		1		µA

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AC Electrical Characteristics

All typical values are for V_{CC} = 3.3V and T_A = 25°C unless otherwise specified.

Symbol	Description	Test Conditions	V_{CC} (V)	T_A = -40°C to +85°C			Units
				Min.	Typ.	Max.	
t_{INIT}	Initialization Time V_{CC} to Output(1)	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.6V	1.5 to 3.6		60		µs
t_{EN}	Enable Time $\overline{OE}$ to Output	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.6V	1.5 to 3.6		60	150	µs
t_{DIS}	Disable Time $\overline{OE}$ to Output	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.6V	1.5 to 3.6		35	250	ns
t_{ON}	Turn-On Time SEL to Output	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.6V	1.5 to 3.6		350	1100	ns
t_{OFF}	Turn-Off Time SEL to Output	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.6V	1.5 to 3.6		125	800	ns
t_{BBM}	Break-Before-Make Time	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.6V	1.5 to 3.6			450	ns
t_{PD}	Propagation Delay(1)	C_L = 0pF, R_L = 50Ω	1.5 to 3.6			0.25	ns
O_{IRR}	Off Isolation for MIPI(1)	R_L = 50Ω, f = 1250MHz, $\overline{OE}$ = HIGH, V_{SW} = 0.5V	1.5 to 3.6		-28		dB
X_{TALK}	Crosstalk for MIPI(1)	R_L = 50Ω, f = 1250MHz, SEL = HIGH, V_{SW} = 0.5V	1.5 to 3.6		-35		dB
I_{LOSS}	Insertion Loss(1)	R_L = 50Ω, C_L = 0pF, f = 1250MHz, V_{SW} = 0.5V	1.5 to 3.6		-0.7		dB
BW	-3db Bandwidth(1)	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.5V	1.5 to 3.6	5	6		GHz

Note:

1. Guaranteed by characterization.

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High-Speed-Related AC Electrical Characteristics

Symbol	Description	Test Conditions	V_{CC} (V)	T_A = -40°C to +85°C			Units
				Min.	Typ.	Max.	
$t_{SK(P)}$	D-PHY HS Mode Skew of Opposite Transitions of the Same Output[1]	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.3V	1.5 to 3.6		4	8	ps
	C-PHY HS Mode Skew of 3 channels in same lane	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.5V	1.5 to 3.6		4		
	D-PHY HS Mode Skew of all group A or group B channels[1]	R_L = 50Ω, C_L = 0pF, V_{SW} = 0.3V	1.5 to 3.6		6	10	

Note:
1. Guaranteed by characterization.

Capacitance

Symbol	Description	Test Conditions	T_A = -40°C to +85°C			Units
			Min.	Typ.	Max.	
C_{IN}	Control Pin Input Capacitance[1]	V_{CC} = 0V, f = 1MHz		2.1		pF
C_{ON}	On Capacitance[1]	V_{CC} = 3.3V, $\overline{OE}$ = 0V, f = 1250MHz (In HS common value)		1.3		pF
C_{OFF}	Off Capacitance[1]	V_{CC} or $\overline{OE}$ = 3.3V, f = 1250MHz (Both sides in HS common value)		0.8		pF

Note:
1. Guaranteed by characterization.

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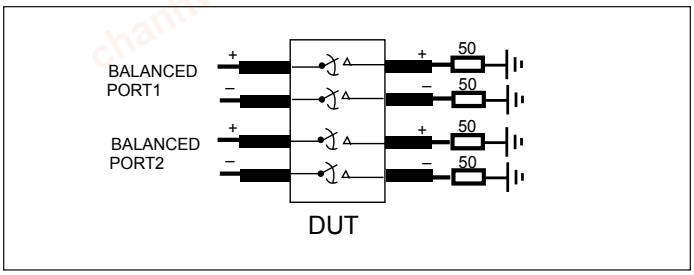


Figure 1. Crosstalk Setup

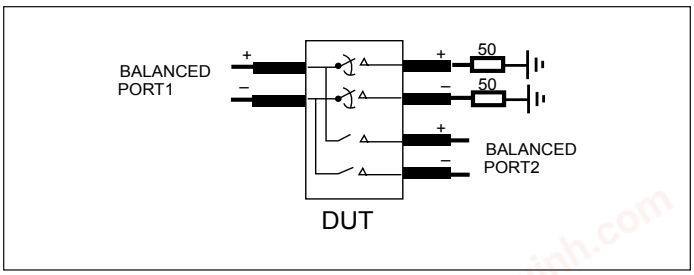


Figure 2. Off-Isolation Setup

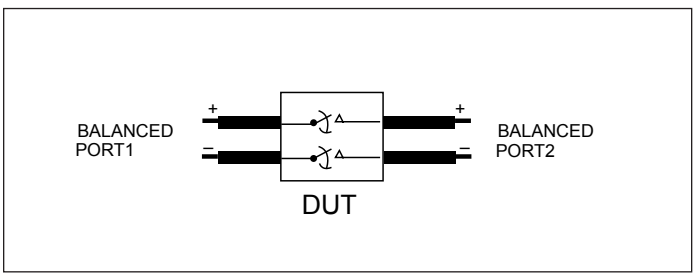


Figure 3. Differential Insertion Loss

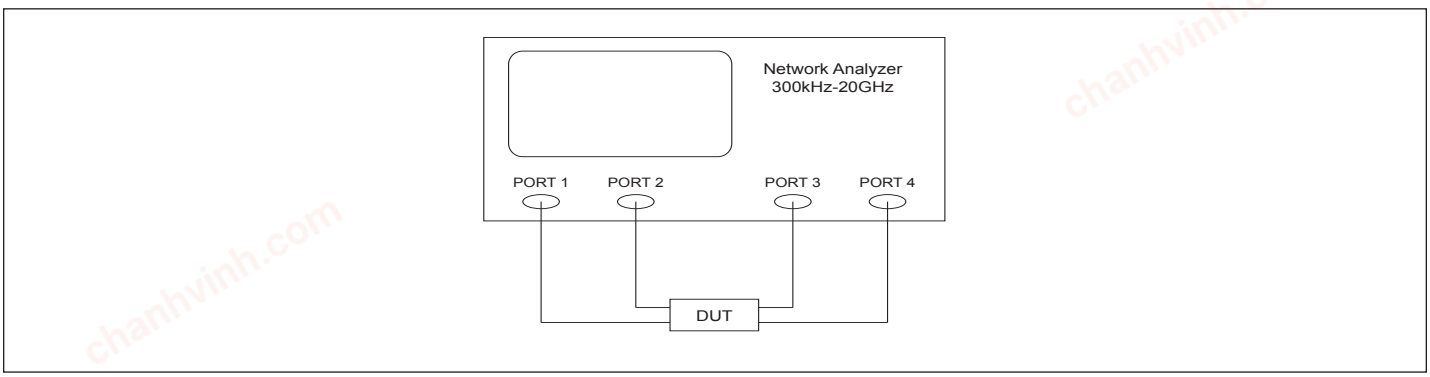
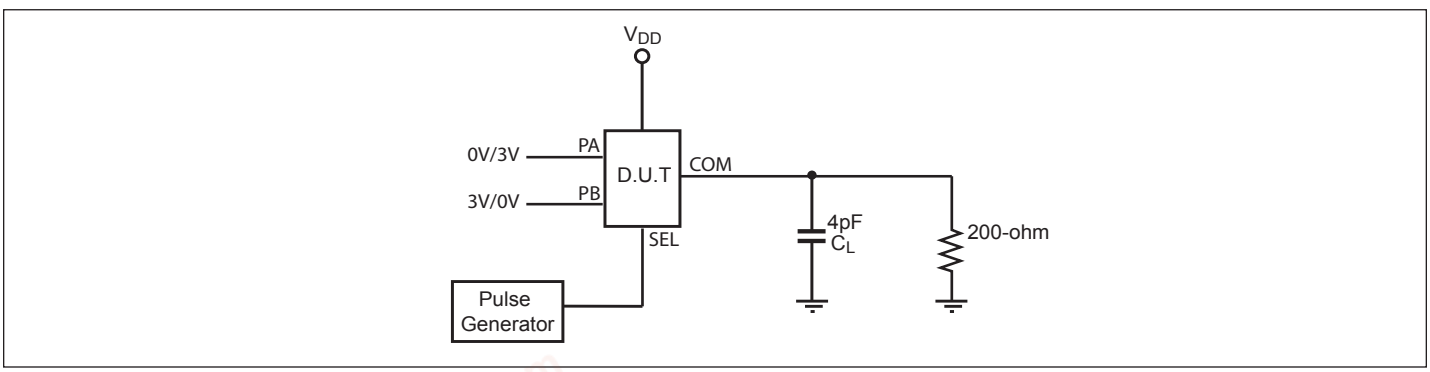


Figure 4. Test Circuit for Dynamic Electrical Characteristics

Test Circuit for Electrical Characteristics



Notes:

1. C_L = Load capacitance: includes jig and probe capacitance.
2. R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator
3. All input impulses are supplied by generators having the following characteristics: PRR ≤ MHz, $Z_O = 50\Omega$, $t_R \leq 2.5$ns, $t_F \leq 2.5$ns.
4. The outputs are measured one at a time with one transition per measurement.

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Switching Waveforms

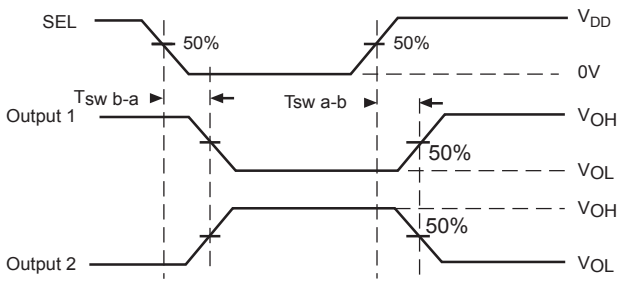


Figure 5. Voltage Waveforms for Select Timing

Test Condition

Output 1 Test Condition	Output 2 Test Condition
PA = Low	PA = High
PB = High	PB = Low

Part Marking

WVR62
6XEBE
YWXX̄

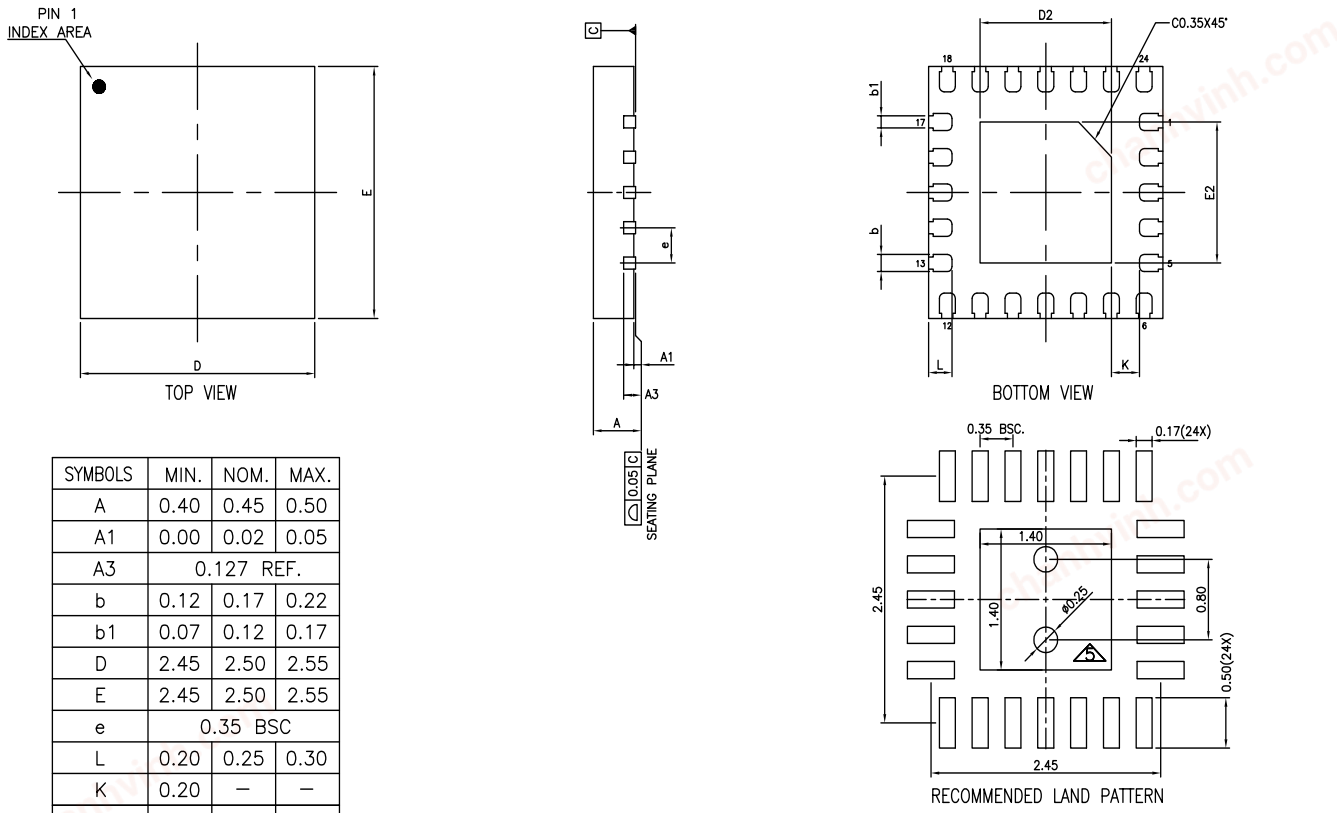
Y: Shortened Date Code (Year)
W: Shortened Date Code (Workweek)
1st X: Assembly Code
2nd X: Fab Code

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Packaging Mechanical

24-X1QFN (XEB)



SYMBOLS	MIN.	NOM.	MAX.
A	0.40	0.45	0.50
A1	0.00	0.02	0.05
A3		0.127 REF.	
b	0.12	0.17	0.22
b1	0.07	0.12	0.17
D	2.45	2.50	2.55
E	2.45	2.50	2.55
e		0.35 BSC	
L	0.20	0.25	0.30
K	0.20	–	–
D2	1.35	1.40	1.45
E2	1.35	1.40	1.45

NOTE :
1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
2. COPLANARITY APPLIES TO THE EXPOSED THERMAL PAD AS WELL AS THE TERMINALS.
3. REFER JEDEC MO-288
4. RECOMMENDED LAND PATTERN IS FOR REFERENCE ONLY.
5. THERMAL PAD SOLDERING AREA

DATE: 06/26/19

DESCRIPTION: 24-Contact, Extra Thin Fine Pitch QFN, X1QFN

PACKAGE CODE: XEB (XEB24)

DOCUMENT CONTROL #: PD-2243 REVISION: –

20-0457

For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Code	Package Code	Package Description
PI3WVR626XEBEX	XEB	24-Contact, Extra Thin Fine Pitch (X1QFN) QFN

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. E = Pb-free and Green
5. X suffix = Tape/Reel

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